

Silicon PNP Power Transistors

2SA887

DESCRIPTION

- With TO-202 package
- Complement to type 2SC1848

APPLICATIONS

- Medium power amplifier

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

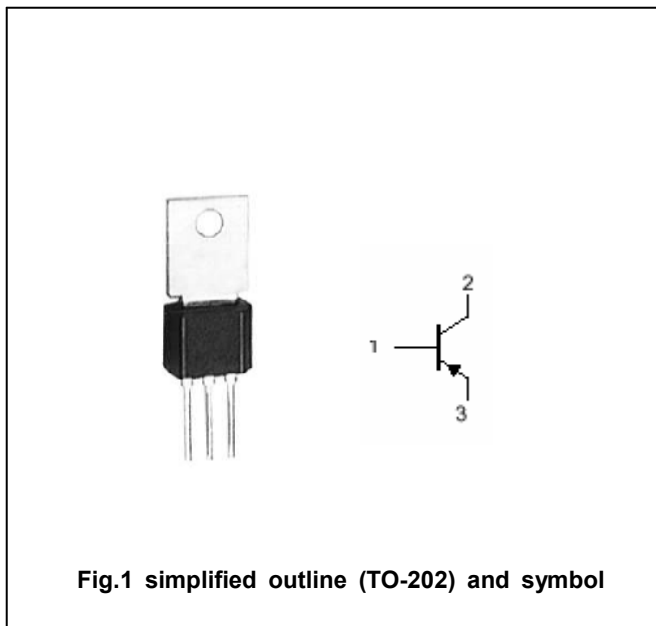


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-70	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-3	A
P _C	Collector power dissipation	T _a =25°C	1.2	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA; I _E =0	-70			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A		-0.6	-1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-0.2A		-1.0	-1.5	V
h _{FE-1}	DC current gain	I _C =-100mA; V _{CE} =-5V	30			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	50		220	
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-1.0	μA
I _{CEO}	Collector cut-off current	V _{CE} =-20V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
f _T	Transition frequency	I _E =0.5A; V _{CB} =-5V		150		MHz

◆ h_{FE-2} Classifications

P	Q	R
50-100	80-160	120-220

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PACKAGE OUTLINE

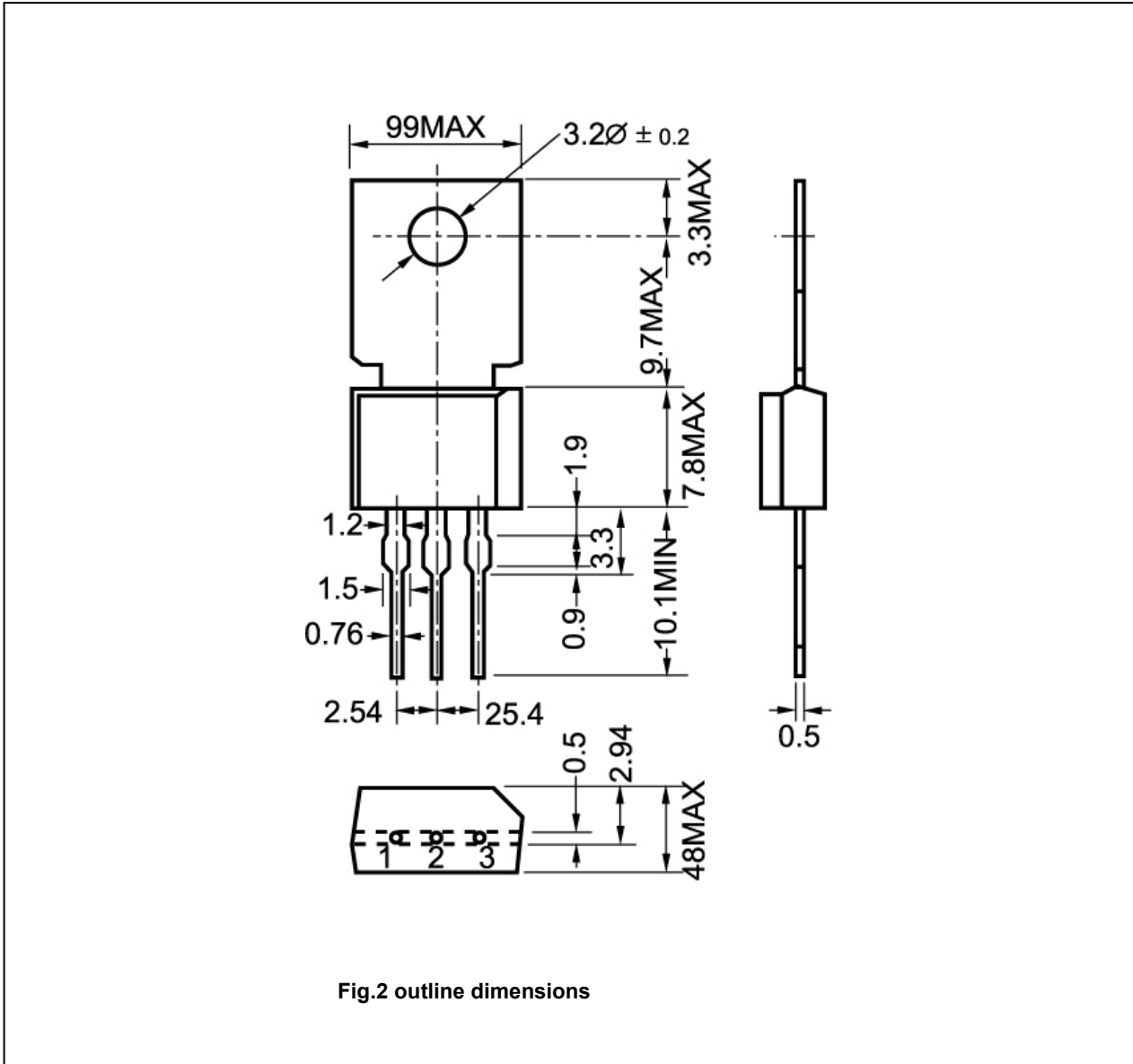


Fig.2 outline dimensions